

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-32. (Canceled)

33. (Currently Amended) A cleaning method for cleaning a photomask having a patterned structure on a surface, comprising:

making a cleaning agent contact a surface of the photomask, and

applying a force on the surface by moving the cleaning agent on the surface to remove particles on the surface so that the surface being free of particle of 0.15 μm or larger,

wherein said cleaning agent is in a liquid state not containing 0.1 μm or larger particles and having a viscosity of 50 to 700 mPa•s.

34. (Currently Amended) The cleaning method according to claim 33, wherein the cleaning agent is in a liquid state not containing 0.1 μm or larger particles by being subjected to filtration.

35. (Currently Amended) The cleaning method according to claim 33, wherein the force is generated by the movement of the liquid caused by the relative motion of a member in contact with the liquid, but not in contact with the photomask, and the photomask.

36-37. (Canceled)

38. (Currently Amended) The cleaning method according to claim 33, wherein the liquid contains polyoxyethylene alkyl ether and alkaline builder.

39. (Previously Presented) The cleaning method according to claim 33, wherein the liquid has a viscosity of 100 to 400mPa•s.

40. (Previously Presented) The cleaning method according to claim 33, wherein the liquid has a viscosity of 200 to 300mPa•s.

41. (Previously Presented) The cleaning method according to claim 33, wherein the liquid has a pH value which makes the zeta potential of both of the surface of the object and that of a particle to be removed from the surface of homopolar.

42. (Previously Presented) The cleaning method according to claim 33, wherein the liquid has a pH value of at least 6.

43. (Previously Presented) The cleaning method according to claim 33, wherein the liquid has a pH value of at least 9.

44. (Currently Amended) The cleaning method according to claim 33, wherein the photo-mask has a recessed portion formed on an open portion in light shielding film on a glass substrate.

45. (Currently Amended) The cleaning method according to claim 33, wherein the photo-mask has a pattern formed by a film containing MoSi and the cleaning agent contains KOH or NaOH.

46. (Previously Presented) The cleaning method according to claim 34, wherein the liquid is moved on the surface by rotation of the object, declination of the object, continuous supply of the liquid on the object, swinging of the object or blowing of the liquid on the object.

47. (Previously Presented) The cleaning method according to claim 34, wherein the liquid is moved on the surface by supplying another liquid having lower viscosity than the liquid.

48. (Previously Presented) The cleaning method according to claim 33, wherein the liquid comprises a water soluble compound selected from the group consisting of polymeric glycol, ethylene oxide additives and propylene additives of polyatomic alcohol and nonionic surfactant.

49-67. (Canceled)

68. (Currently Amended) A cleaning agent in a liquid state for cleaning a surface of a patterned photo-mask, having a viscosity of 50 to 700 mPa•s and not containing 0.1 μm or larger particles so that the surface being free of particle of 0.15 μm or larger.

69. (Previously Presented) The cleaning agent according to claim 68, wherein the pH value of the agent is 6 or higher.

70. (Canceled)

71. (Currently Amended) The cleaning agent according to claim 68, wherein the liquid comprises at least one water soluble compound selected from the group consisting of polymeric glycol, ethylene oxide additives and propylene additives of polyatomic alcohol and nonionic surfactant.